

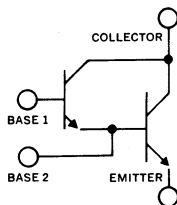
POWER DARLINGTONS

2 Amp, 300V, Planar NPN

U2T712
U2T713
U2T722
U2T723

FEATURES

- High Current Gain: up to 1000 min. @ $I_C = 1A$
- Low Saturation Voltage: as low as 1.5V max. @ $I_C = 2A$
- High Voltage: up to 300V. min. V_{CE0}
- Peak Current: to 5A
- Monolithic Planar Chip Construction



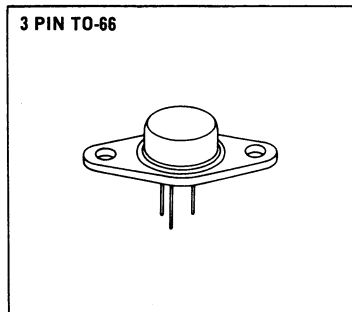
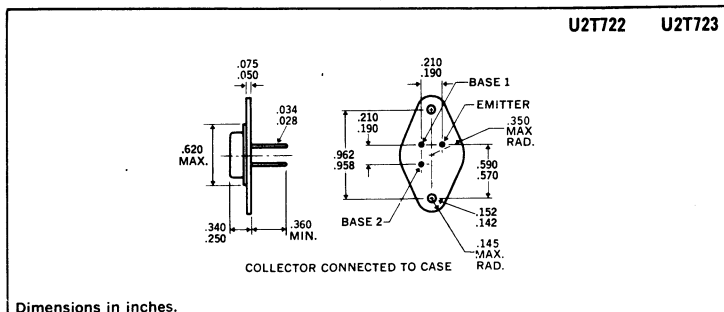
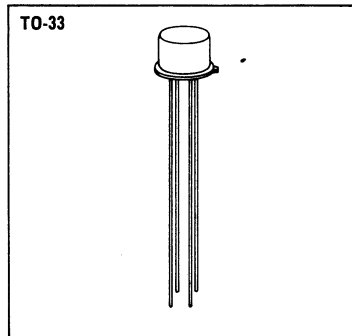
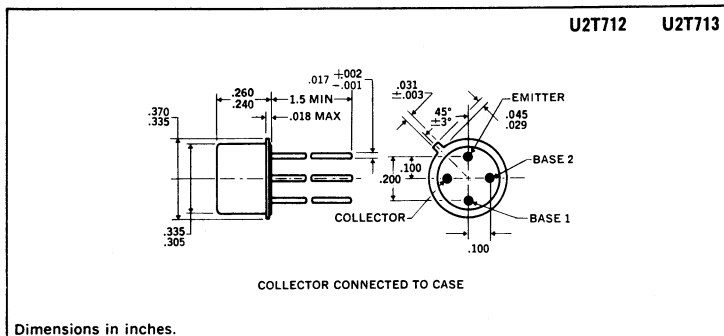
DESCRIPTION

Unitrode NPN Darlington's consist of a two transistor circuit on a single monolithic planar chip.

ABSOLUTE MAXIMUM RATINGS

	TO-33		3 PIN TO-66	
	U2T712	U2T713	U2T722	U2T723
Collector — Emitter Voltage	200V	300V	200V	300V
Emitter — Base Voltages				
V_{EB2}	6V	6V	6V	6V
V_{EB1}	12V	12V	12V	12V
D.C. Collector Current	2A	2A	2A	2A
Peak Collector Current	5A	5A	5A	5A
Base 1 Current	0.5A	0.5A	0.5A	0.5A
Power Dissipation				
25°C Ambient	1W	1W	2W	2W
100°C Case	5W	5W	20W	20W
Thermal Resistance				
Junction-to-Case	20°C/W		5°C/W	
Operating and Storage Temperature Range	-65°C to 200°C		-65°C to 200°C	

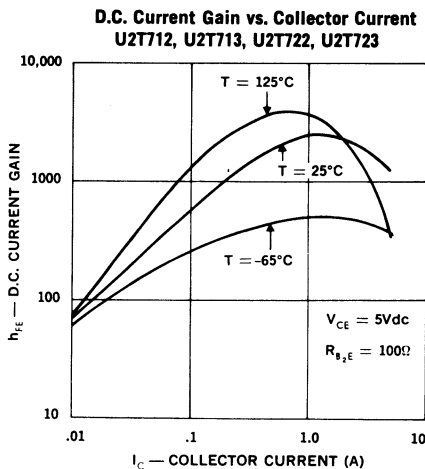
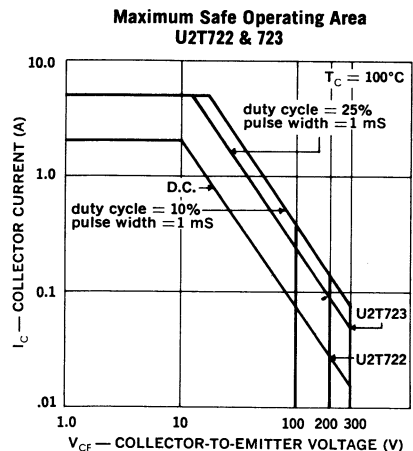
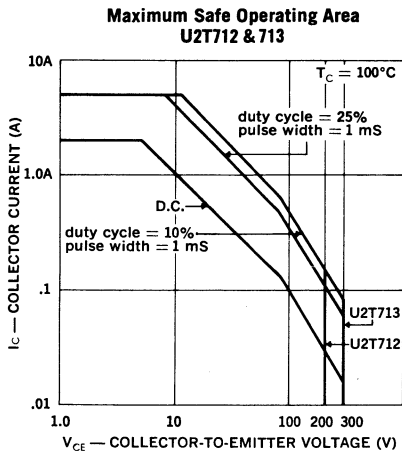
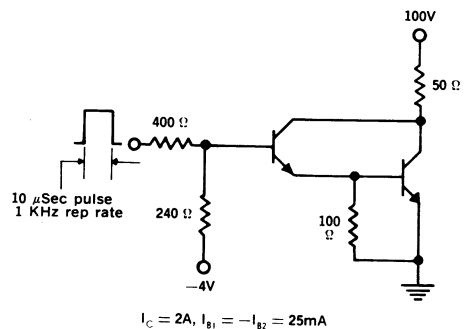
MECHANICAL SPECIFICATIONS



ELECTRICAL SPECIFICATIONS (at 25°C unless noted)

Test	Symbol	U2T712 & 722 Min. Max.	U2T713 & 723 Min. Max.	Units	Test Conditions
D.C. Current Gain (Note 1)	h_{FE}	1000 —	1000 —	—	$I_C = 1A, V_{CE} = 5V, R_{B2E} = 1K$
Collector Saturation Voltage (Note 1)	$V_{CE(sat)}$	— 1.5	— 1.5	V	$I_C = 2A, R_{B2E} = 100, I_{B1} = 20mA$
Collector-Emitter Breakdown Voltage (Note 1)	BV_{CEO}	200 —	300 —	V	$I_C = 10mA$
	BV_{CER}	250 Typ.	350 Typ.	V	$I_C = 10mA, R_{B1E} = 2.2K, R_{B2E} = 100$
Collector Cutoff Current	I_{CER}	— 10.0	— 10.0	μA	$R_{B1E} = 2.2K, R_{B2E} = 100$ U2T712 & 722: $V_{CE} = 200$ U2T713 & 723: $V_{CE} = 300$
Collector Capacitance	C_{obo}	— 100	— 100	pf	$V_{CB1} = 10V, I_E = 0, f = 1MHz$
A.C. Current Gain	h_{fe}	4.0 Typ.	4.0 Typ.	—	$I_C = 0.5A, V_{CE} = 10V, f = 20MHz, R_{B2E} = 100$
Rise Time	t_r	0.6 Typ.	0.6 Typ.	μS	$V_{CC} = 100V, I_B(ON) = I_B(OFF) = 25mA,$ $I_C = 2A, R_{B2E} = 100$
Storage Time	t_s	1.5 Typ.	1.5 Typ.	μS	
Fall Time	t_f	1.0 Typ.	1.0 Typ.	μS	

Note 1. Pulse width = 300 μS ; duty cycle $\leq 2\%$

**Switching Speed Circuit**

POWER TRANSISTORS

2 Amp, 500V, Fast Switching
Silicon NPN Mesa

UMT3584
UMT3585

FEATURES

- Collector Base Voltage: up to 500V
- Peak Collector Current: 5A
- Rise Time $\leq 3\mu s$ } $I_c = 1A$
- Fall Time $\leq 3\mu s$ }
- Economical Plastic Molded Construction

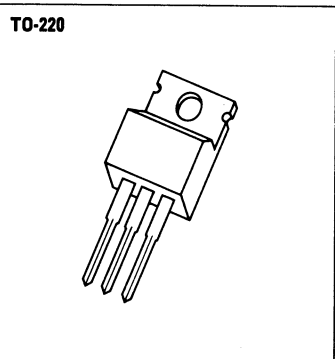
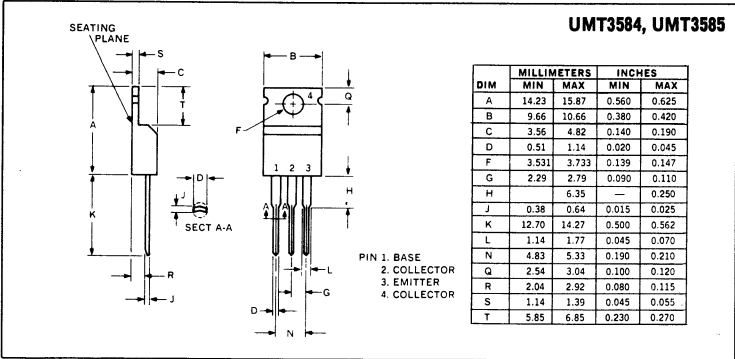
DESCRIPTION

These high voltage triple diffused glass passivated power transistors in a plastic TO-220 package combine fast switching, low saturation voltage and rugged $E_{s/b}$ capability. They are designed for use in off-line switching regulators, converters, inverters and deflection circuitry.

ABSOLUTE MAXIMUM RATINGS

	UMT3584	UMT3585
Collector Base Voltage, V_{CBO}	375V	500V
Collector Emitter Voltage, V_{CEO} (SUS)	250V	300V
Emitter Base Voltage, V_{EBO}	6V	6V
Collector Current, I_C continuous	2A	2A
I_{CM} peak	5A	5A
D.C. Base Current, continuous	1A	1A
Power Dissipation, P_T 25°C Case	35W	35W
Operating and Storage Temperature Range	-65 to +150°C	

MECHANICAL SPECIFICATIONS



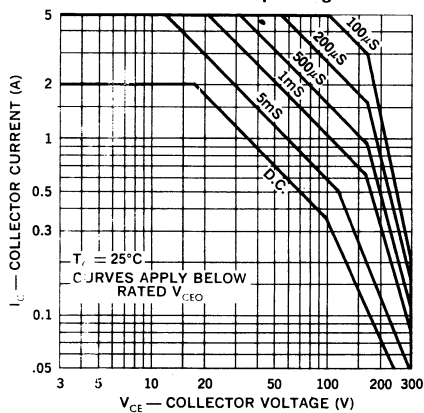
ELECTRICAL SPECIFICATIONS (at 25°C unless noted)

Test	Symbol	UMT3584		UMT3585		Units	Test Conditions
		MIN.	MAX.	MIN.	MAX.		
D.C. Current Gain (Note 1)	h_{FE}	40	—	40	—		$I_C = 100\text{mA}$, $V_{CE} = 10\text{V}$
		8	80	8	80		$I_C = 1\text{A}$, $V_{CE} = 2\text{V}$
		25	100	25	100		$I_C = 1\text{A}$, $V_{CE} = 10\text{V}$
Collector Saturation Voltage (Note 1)	$V_{CE(sat)}$	—	0.75	—	0.75	V	$I_C = 1\text{A}$, $I_B = 125\text{mA}$
Base Saturation Voltage (Note 1)	$V_{BE(sat)}$	—	1.4	—	1.4	V	$I_C = 1\text{A}$, $I_B = 100\text{mA}$
Collector-Emitter Sustaining Voltage (Note 2)	$V_{CEO(sus)}$	250	—	300	—	V	$I_C = 200\text{mA}$
Collector-Emitter Sustaining Voltage (See Note 2)	$V_{CER(sus)}$	300	—	400	—	V	$I_C = 200\text{mA}$ $R_{BE} = 200\Omega$
Emitter Cutoff Current	I_{EO}	—	0.5	—	0.5	mA	$V_{BE} = -6\text{V}$
Collector-Cutoff Current	I_{CEO}	—	5.0	—	5.0	mA	$V_{CE} = 150\text{V}$
Collector-Cutoff Current	I_{CEV}	—	1.0	—	—	mA	$V_{CE} = 340\text{V}$, $V_{BE} = -1.5\text{V}$
		—	—	—	1.0		$V_{CE} = 450\text{V}$, $V_{BE} = -1.5\text{V}$
Collector Cutoff Current, 150°C	I_{CEV}	—	3.0	—	3.0	mA	$V_{CE} = 300\text{V}$, $V_{BE} = -1.5\text{V}$
Small Signal Forward Transfer Ratio	h_{fe}	3	—	3	—	—	$I_C = 200\text{mA}$, $V_{CE} = 10\text{V}$ $f = 5\text{MHz}$
Collector Capacitance	C_{ob}	—	120	—	120	pF	$V_{CB} = 10\text{V}$, $f = 1\text{MHz}$
Second Breakdown Collector Current	$I_{S/b}$	350	—	350	—	mA	$V_{CE} = 100\text{V}$
Second Breakdown Energy	$E_{S/b}$	200	—	200	—	μJ	$I_C = 2\text{A}$ $R_{BE} = 20\Omega$ $L = 100\mu\text{H}$
Switching Speeds	Rise Time	—	3.0	—	3.0	μs	$I_C = 1\text{A}$ $I_{B1} = I_{B2} = 100\text{mA}$ $V_{CC} = 200\text{V}$
	Storage Time	—	4.0	—	4.0		
	Fall Time	—	3.0	—	3.0		
Thermal Resistance: Junction-to-Case	$R_{\theta JC}$	—	3.57	—	3.57	°C/W	
Junction-to-Ambient	$R_{\theta JA}$	—	70	—	70	°C/W	

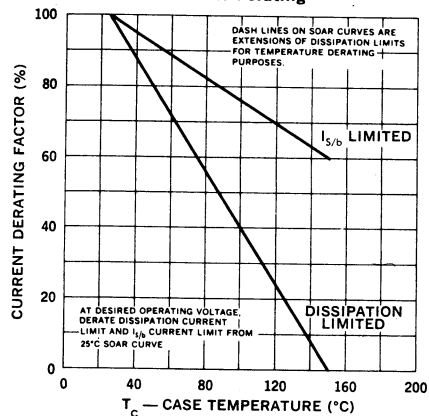
Notes

1. Pulse length = 250 μs ; duty cycle $\leq 1\%$.
2. Sustaining Voltage. Measured at a high current point where collector-emitter voltage is lowest. Current pulse length $\cong 50\text{ }\mu\text{s}$; duty cycle $\leq 1\%$. Voltage clamped at maximum collector-emitter voltage.

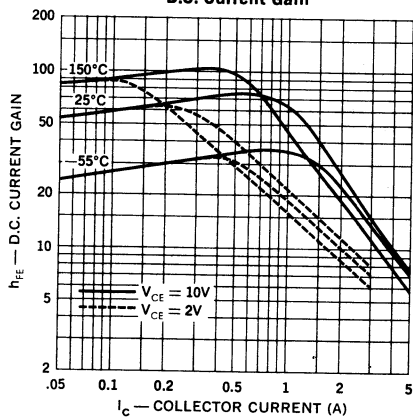
Forward Bias Safe Operating Area



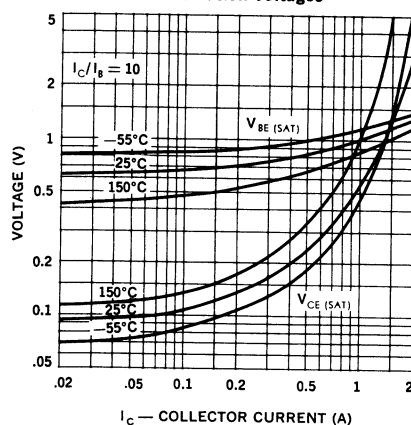
Power Derating



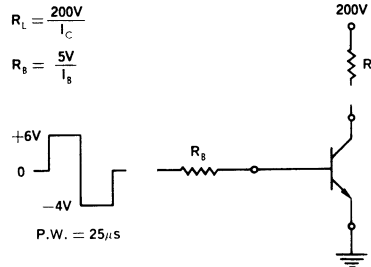
D.C. Current Gain



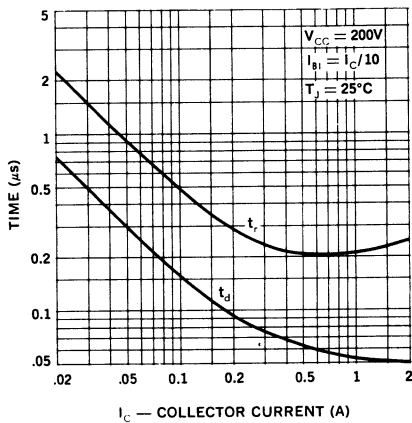
Saturation Voltages



Switching Time Test Circuit



Turn-On Time



Turn-Off Time

